

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1.-13. (Canceled)

14. (Previously Presented) A luminescent device comprising:

a thin film transistor provided over an insulating surface;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer containing an alkaline metal;

an anode; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline metal.

15. (Currently Amended) A luminescent device according to claim 14, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

16. (Currently Amended) A luminescent device according to claim 14, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

17. (Currently Amended) A luminescent device according to claim 14, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film

containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

18. (Currently Amended) A luminescent device according to claim 14, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

19. (Withdrawn) A luminescent device comprising:  
a thin film transistor provided over an insulating surface;  
a luminescent element electrically connected with said thin film transistor, comprising:  
an organic compound layer;  
an anode;  
a buffer layer containing an alkaline metal; and  
a cathode; and  
at least one insulating layer provided between said thin film transistor and said luminescent element,  
wherein said insulating layer is capable of adsorbing said alkaline metal.

20. (Withdrawn) A device according to claim 19, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

21. (Withdrawn) A device according to claim 19, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

22. (Withdrawn) A device according to claim 19, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

23. (Withdrawn) A device according to claim 19, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

24. (Withdrawn) A luminescent device comprising:  
a thin film transistor provided over an insulating surface;  
a luminescent element electrically connected with said thin film transistor, comprising:  
an organic compound layer;  
an anode; and  
a cathode containing an alkaline-earth metal; and  
at least one insulating layer provided between said thin film transistor and said luminescent element,  
wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

25. (Withdrawn) A device according to claim 24, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

26. (Withdrawn) A device according to claim 24, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

27. (Withdrawn) A device according to claim 24, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

28. (Withdrawn) A device according to claim 24, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

29. (Withdrawn) A luminescent device comprising:  
a thin film transistor provided over an insulating surface;  
a luminescent element electrically connected with said thin film transistor,  
comprising:

- an organic compound layer containing an alkaline-earth metal;
- an anode; and
- a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

30. (Withdrawn) A device according to claim 29, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

31. (Withdrawn) A device according to claim 29, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

32. (Withdrawn) A device according to claim 29, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

33. (Withdrawn) A device according to claim 29, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

34. (Withdrawn) A luminescent device comprising:  
a thin film transistor provided over an insulating surface of a substrate;  
a luminescent element electrically connected with said thin film transistor, comprising:  
an organic compound layer;  
an anode;  
a buffer layer containing an alkaline-earth metal; and  
a cathode; and  
at least one insulating layer provided between said thin film transistor and said luminescent element  
wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

35. (Withdrawn) A device according to claim 34, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

36. (Withdrawn) A device according to claim 34, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

37. (Withdrawn) A device according to claim 34, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

38. (Withdrawn) A device according to claim 34, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

39. (New) A luminescent device comprising:  
a thin film transistor provided over an insulating surface;  
a luminescent element electrically connected with said thin film transistor,  
comprising:  
an organic compound layer containing an alkaline metal;  
an anode; and  
a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline metal, and  
wherein said organic compound layer comprises a hole implantation layer.

40. (New) A luminescent device according to claim 39, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

41. (New) A luminescent device according to claim 39, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

42. (New) A luminescent device according to claim 39, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

43. (New) A luminescent device according to claim 39, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

44. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface;  
a luminescent element electrically connected with said thin film transistor,  
comprising:

an organic compound layer containing an alkaline metal;  
an anode; and  
a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline metal, and  
wherein said organic compound layer comprises a hole implantation layer.

45. (New) A luminescent device according to claim 44, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

46. (New) A luminescent device according to claim 44, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

47. (New) A luminescent device according to claim 44, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

48. (New) A luminescent device according to claim 44, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

49. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer containing an alkaline metal and an inorganic material;

an anode; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline metal.

50. (New) A luminescent device according to claim 49, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

51. (New) A luminescent device according to claim 49, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

52. (New) A luminescent device according to claim 49, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

53. (New) A luminescent device according to claim 49, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

54. (New) A luminescent device comprising:  
a thin film transistor provided over an insulating surface;  
a luminescent element electrically connected with said thin film transistor, comprising:  
an organic compound layer containing an alkaline metal and an inorganic material;  
an anode; and  
a cathode; and  
at least one insulating layer provided between said thin film transistor and said luminescent element,  
wherein said insulating layer is capable of adsorbing said alkaline metal, and

wherein said organic compound layer comprises a hole implantation layer.

55. (New) A luminescent device according to claim 54, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

56. (New) A luminescent device according to claim 54, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

57. (New) A luminescent device according to claim 54, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

58. (New) A luminescent device according to claim 54, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.